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October 2013

FQD5P20 / FQU5P20 P-Channel QFET® MOSFET

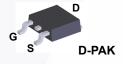
-200 V, -3.7 A, 1.4 Ω

Description

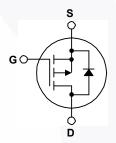
This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications

Features

- -3.7 A, -200 V, $R_{DS(on)}$ = 1.4 Ω (Max.)@ V_{GS} = -10 V, I_D =-1.85 A
- Low Gate Charge (Typ. 10 nC)
- Low Crss (Typ. 12 pF)
- 100% Avalanche Tested
- RoHS Compliant







Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		FQD5P20TM / FQU5P20TU	Unit
V _{DSS}	Drain-Source Voltage		-200	V
I _D	Drain Current - Continuous (T _C = 25°	°C)	-3.7	Α
	- Continuous (T _C = 100	0°C)	-2.34	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	-14.8	Α
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	330	mJ
I _{AR}	Avalanche Current	(Note 1)	-3.7	Α
E _{AR}	Repetitive Avalanche Energy	(Note 1)	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-5.5	V/ns
P _D	Power Dissipation (T _A = 25°C) *		2.5	W
_	Power Dissipation (T _C = 25°C)		45	W
- Derate above 25°C			0.36	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQD5P20TM FQU5P20TU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 2.78		
Р	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (* 1 in ² pad of 2 oz copper), Max.	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQD5P20	FQD5P20TM	DPAK	330 mm	16 mm	2500
FQU5P20	FQU5P20TU	IPAK	-	-	70

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-200			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-0.17		V/°C
I _{DSS} z	Zero Gate Voltage Drain Current	V _{DS} = -200 V, V _{GS} = 0 V			-1	μА
		V _{DS} = -160 V, T _C = 125°C			-10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-3.0		-5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10•V, I _D = -1.85 A		1.1	1.4	Ω
g _{FS}	Forward Transconductance	V _{DS} = -40 V, I _D = -1.85 A		2.2		S
	Input Capacitance Output Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		330 75	430 98	
Coss	Output Capacitance			75	98	pF
C _{rss}	Reverse Transfer Capacitance			12	15	pF
Switch	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = -100 V, I _D = -4.8 A,		9	28	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		70	150	ns
t _{d(off)}	Turn-Off Delay Time	11.6 - 20 32	/	12	35	ns
t _f	Turn-Off Fall Time	(Note 4)		25	60	ns
. ,	Turn-Off Fall Time Total Gate Charge	, ,		25 10	60 13	
t _f		V _{DS} = -160 V, I _D = -4.8 A,		_		nC
t _f Q _g	Total Gate Charge	, ,		10	13	nC nC
t _f Q _g Q _{gs} Q _{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DS} = -160 \text{ V}, I_{D} = -4.8 \text{ A},$ $V_{GS} = -10 \text{ V}$ (Note 4)		10	13	nC nC nC
t _f Q _g Q _{gs} Q _{gd}	Total Gate Charge Gate-Source Charge	V_{DS} = -160 V, I_{D} = -4.8 A, V_{GS} = -10 V (Note 4)		10	13	nC nC
$egin{array}{l} t_{\mathrm{f}} & & & \\ Q_{\mathrm{g}} & & & \\ Q_{\mathrm{gs}} & & & \\ Q_{\mathrm{gd}} & & & & \\ & & & & \\ & & & & \\ & & & &$	Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics ar	V _{DS} = -160 V, I _D = -4.8 A, V _{GS} = -10 V (Note 4)		10 2.8 5.2	13	nC nC
$egin{array}{l} t_{f} & & & \\ Q_{g} & & & \\ Q_{gs} & & & \\ Q_{gd} & & & \\ \hline \textbf{Drain-S} & & & \\ I_{SM} & & & \\ \hline \end{array}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics ar Maximum Continuous Drain-Source Dio	V _{DS} = -160 V, I _D = -4.8 A, V _{GS} = -10 V (Note 4) Ind Maximum Ratings ode Forward Current Forward Current		10 2.8 5.2	-3.7	nC nC nC
$egin{array}{l} t_{\mathrm{f}} & & & \\ Q_{\mathrm{g}} & & & \\ Q_{\mathrm{gs}} & & & \\ Q_{\mathrm{gd}} & & & & \\ & & & & \\ & & & & \\ & & & &$	Total Gate Charge Gate-Source Charge Gate-Drain Charge Source Diode Characteristics ar Maximum Continuous Drain-Source Diode Maximum Pulsed Drain-Source Diode F	V _{DS} = -160 V, I _D = -4.8 A, V _{GS} = -10 V (Note 4)		10 2.8 5.2	-3.7 -14.8	nC nC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature 2. L = 36.2mH, I_{AS} = -3.7A, V_{DD} = -50V, R_G = 25 Ω , Starting T_J = 25°C 3. I_{SD} \leq -4.8A, di/dt \leq 300A/μs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C 4. Essentially independent of operating temperature

Typical Characteristics

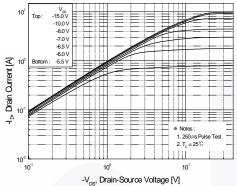


Figure 1. On-Region Characteristics

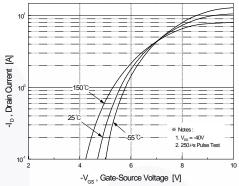


Figure 2. Transfer Characteristics

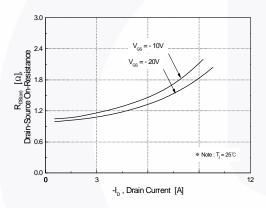


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

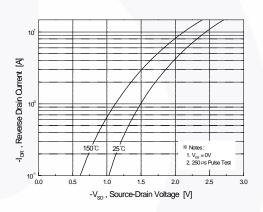


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

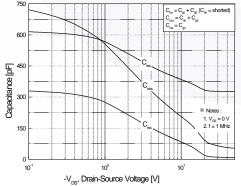


Figure 5. Capacitance Characteristics

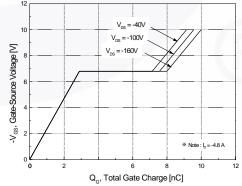


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued) -BV _{DSS} , (Normalized) Drain-Source Breakdown Voltage R_{DS(DN)} , (Normalized) Drain-Source On-Resistance 1. V_{cs} = 0 V 2. I_p = -250 µA 0.8 L -100 0.0 L -100 200 100 150 200 100 150 T_J , Junction Temperature [°C] T_J , Junction Temperature [°C] Figure 7. Breakdown Voltage Variation Figure 8. On-Resistance Variation vs. Temperature vs. Temperature Drain Qurrent [A] -I_D, Drain Qurrent [A] ٩ T_c, Case Temperature [°C] -V_{DS}, Drain-Source Voltage [V] Figure 9. Maximum Safe Operating Area Figure 10. Maximum Drain Current vs. Case Temperature $Z_{\theta JC}(t)$, Thermal Response [$^{O}C/W$] 10 10 10 10 10 10 t, Square Wave Pulse Duration [sec]

Figure 11. Transient Thermal Response Curve



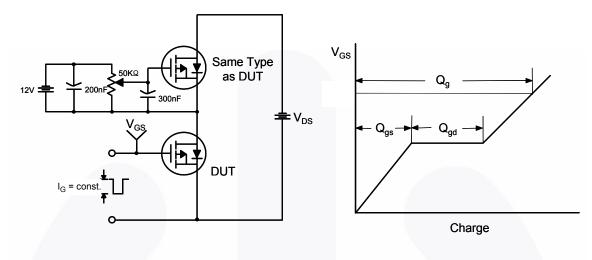


Figure 13. Resistive Switching Test Circuit & Waveforms

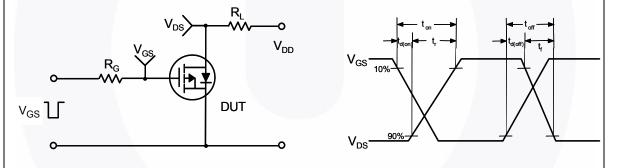
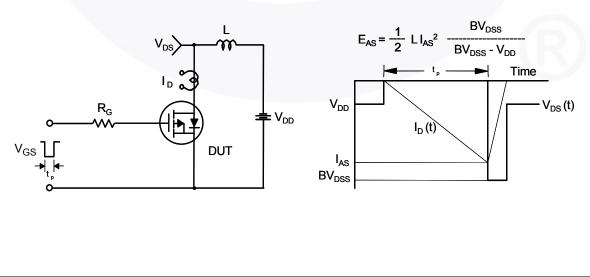
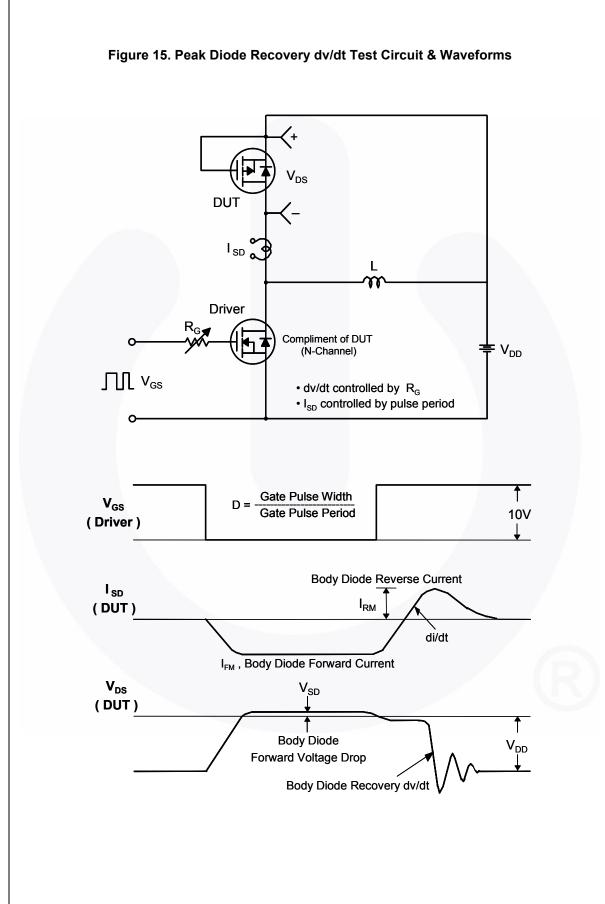


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



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Mechanical Dimensions

TO-252 3L (DPAK)

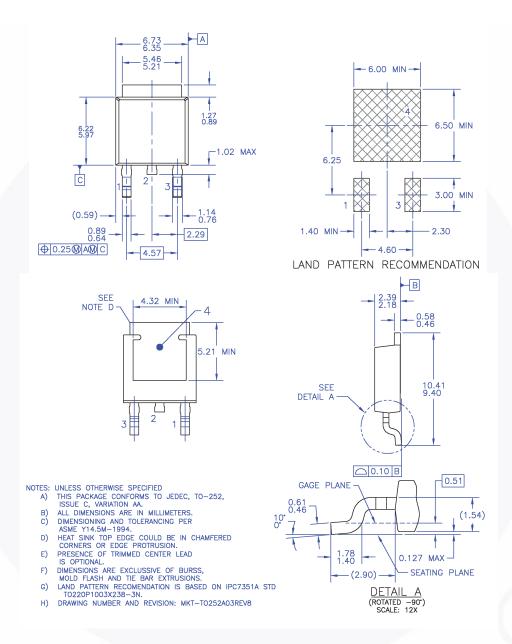


Figure 16. TO252 (D-PAK), Molded, 3 Lead, Option AA&AB

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Dimension in Millimeters

Mechanical Dimensions

TO-251 3L (IPAK)

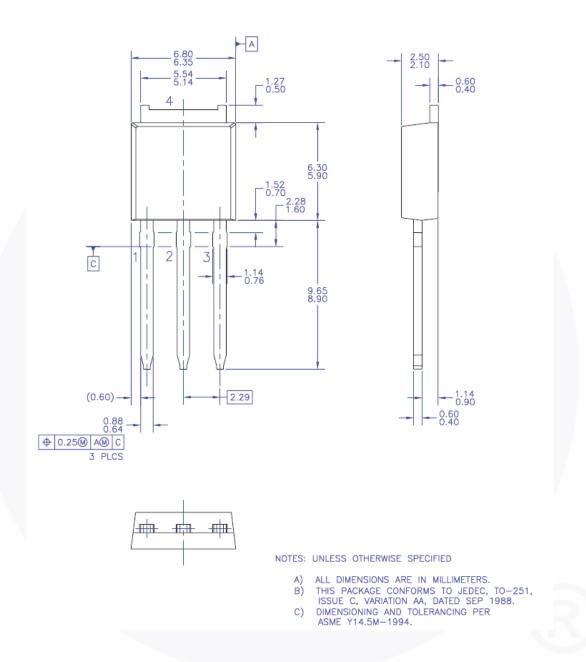


Figure 17. TO251 (IPAK) Molded 3 Lead

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Dimension in Millimeters





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